



Ruttonsha International Rectifier Ltd.

SILICON CONTROLLED RECTIFIERS

High Power Thyristor Hockey Puk Version R/Q-PUK Series

Types : 2500 PR/PQ ...

FEATURES

- ❖ Center amplifying gate.
- ❖ Metal case with ceramic insulator
- ❖ High profile hockey - puk.

TYPICAL APPLICATIONS

- ❖ DC motor control (e.g. for machine tools).
- ❖ Controlled rectifiers (e.g. for battery charging, Uninterrupted Power Supply).
- ❖ AC controllers (e.g. for temperature control, lights control).

Major Ratings and Characteristics

Parameter	2500PR/PQ	Units
$I_{T(AV)}$	2500	A
@ T_{hs}	55	°C
$I_{T(RMS)}$	3925	A
@ T_{hs}	55	°C
I_{TSM} @ 50 Hz	27	kA
I^2t @ 50 Hz	3645	KA ² s
V_{DRM}/V_{RRM}	2400 to 3600	V
t_q typical	400	μs
T_J	125	°C

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ELECTRICAL SPECIFICATIONS

2500PR/PQ Series

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max. mA
2500PR/PQ	240	2400/2400	2500	100
	280	2800/2800	2900	
	320	3200/3200	3300	
	360	3600/3600	3700	

On - state Conduction

Parameter	2500PR/PQ	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	2500	A	180° conduction, half sine wave double side cooled
	55	°C	
$I_{T(RMS)}$ Max RMS on-state current	3925	A	DC @ 55°C heatsink temperature double side cooled
I_{TSM} Max. peak, one-cycle non-repetitive surge current	27	KA	t = 10 ms
			Sinusoidal half wave, Initial $T_J = T_J$ max.
I^2t Maximum I^2t for fusing	3645	KA ² s	t = 10 ms
$V_{T(TO)}$ Threshold voltage	1.06	V	$T_J = T_J$ max
r_t On-state slope resistance	0.25	mΩ	$T_J = T_J$ max.
V_{TM} Max. on state voltage	1.71	V	$I_{PK} = 2000A, T_J = T_J$ max, $t_p = 10$ ms sine pulse
I_H Maximum holding current	400	mA	$T_J = 25^\circ C$, anode supply 12 V resistive load
I_L Typical latching current	1000	mA	$T_J = 25^\circ C$, anode supply 12 V resistive load

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Switching

Parameter	2500PR/PQ	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	100	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1\mu s$ $T_J = T_J$ max. anode voltage $\leq 80\% V_{DRM}$
t_q Typical turn-off time	400	μs	$I_{TM} = 1000A$, $T_J = T_J$ max. di/dt = 40A/μs, $V_R = 75V$ dv/dt = 50V/μs, 0.5 V_{DRM} Reapplied, $t_p = 500\mu s$

Blocking

Parameter	2500PR/PQ	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/μs	$T_J = T_J$ max. linear to 80% rated V_{DRM}
I_{RRM} I_{DRM} Max. peak reverse and off-state leakage current	100	mA	$T_J = T_J$ max. rated V_{DRM} / V_{RRM} applied

Triggering

Parameter	2500PR/PQ	Units	Conditions
P_{GM} Maximum peak gate power	30	W	$T_J = T_J$ max., $t_p \leq 5$ ms
$P_{G(AV)}$ Maximum average gate power	5		$T_J = T_J$ max., $f = 50Hz$, $d\% = 50$
I_{GM} Max. peak positive gate current	3.0	A	$T_J = T_J$ max., $t_p \leq 5$ ms
$+V_{GM}$ Maximum peak positive gate voltage	20	V	$T_J = T_J$ max., $t_p \leq 5$ ms
$-V_{GM}$ Maximum peak negative gate voltage	5.0		
I_{GT} DC gate current required to trigger MAX.	250	mA	$T_J = 25^\circ C$ Max.required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode-to-cathode applied
V_{GT} DC gate voltage required to trigger MAX.	3.0	V	$T_J = 25^\circ C$
I_{GD} DC gate current not to trigger	10	mA	$T_J = T_J$ max. Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied
V_{GD} DC gate voltage not to trigger	0.25	V	

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Thermal and Mechanical Specifications

Parameter	2500PR/PQ	Units	Conditions
T_J Max.operating temperature	125	°C	
T_{stg} Max.storage temperature	150		
R_{thJ-hs} Max. thermal resistance, junction to heatsink	0.011	K/W	DC operation double side cooled
F Mounting force, $\pm 10\%$,	40	KN	
wt Approximate weight	1400 / 1050	g	
Case style	R/Q- PUK		See Outline Table

